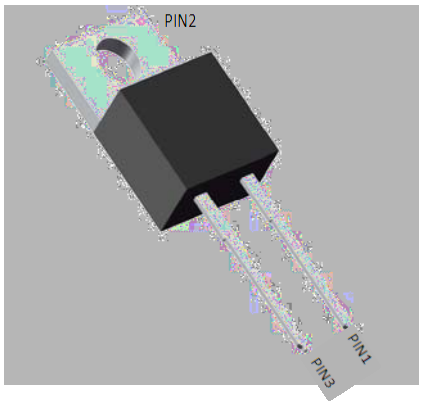
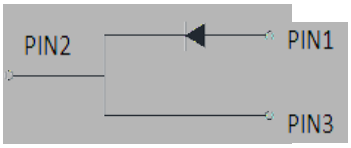




- Adopt FRED chip
- Low forward Voltage drop
- Fast reverse recovery time
- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

- 3 w o: Tin plated leads, solderable per J-STD-002 and JESD22-B102
- : As marked

■ (Tj=25 Unless otherwise specified

Device marking code			MUR1260L
Repetitive Peak Reverse Voltage	V_{RRM}	V	600
Average Rectified Output Current @60Hz sine wave, R-load, T_C(FIG.1)	I_O	A	12
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, T_j=25	I_{FSM}	A	150
Current Squared Time @1ms≤t≤8.3ms Tj=25	I^2t	A^2s	93
Storage Temperature	T_{stg}		-55 ~ +175
Junction Temperature	T_j		-55 ~ +175
Typical Junction capacitance @4V,1MHz	Cj	pF	92

■

Instantaneous forward voltage drop per diode	V_{FM}	V	I_{FM}=12.0A @Tj=25		-	2.4	3.0
			IFM=12.0A @Tj=150		-	2.0	2.4-
DC reverse current at rated DC blocking voltage per diode	I_{RRM1}	uA	VRM=VRRM Tj=25		-	-	10
	I_{RRM2}		VRM=VRRM Tj=150		-	30	200
Reverse Recovery Time	T_{rr}	ns	IF=0.5A IRM=1A IRR=0.25A Tj=25		-	20	25
			Tj=25	IF=12A di/dt=-200A/us VRM=200V	-	34.5	-
			Tj=125		-	66.5	-
Peak recovery current	I_{RRM}	A	Tj=25		-	2.45	-
			Tj=125		-	5.55	-
Reverse recovery charge	Q_{rr}	nC	Tj=25		-	42.5	-
			Tj=125		-	186.5	-

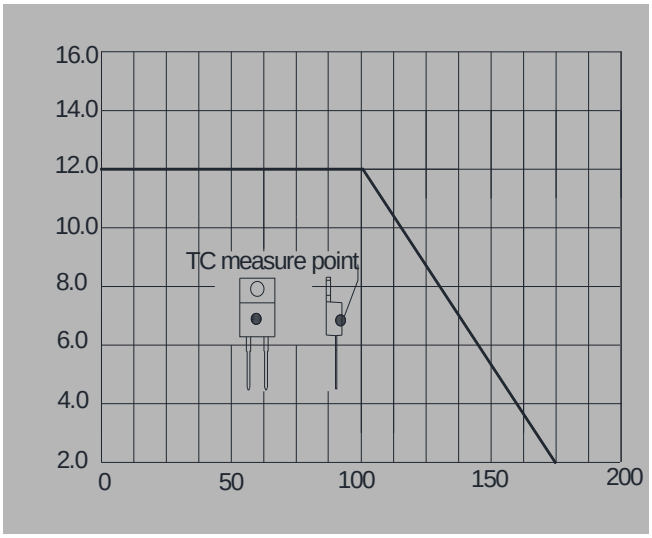
■ Tj=25 Unless otherwise specified

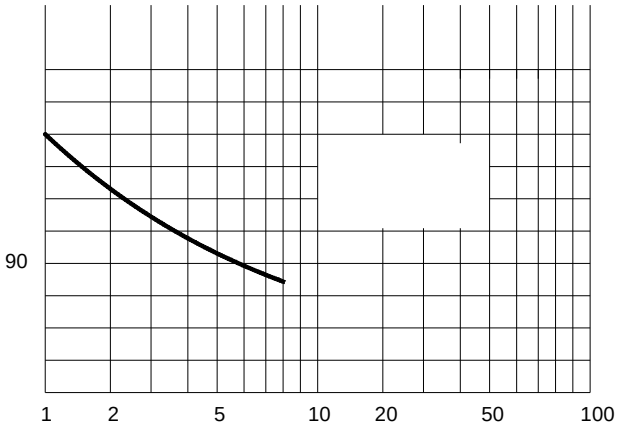
Thermal Resistance	Between junction and case	$R_{\theta J-C}$	/W	2.0
Thermal Resistance	Between junction and Air	$R_{\theta J-A}$	/W	50

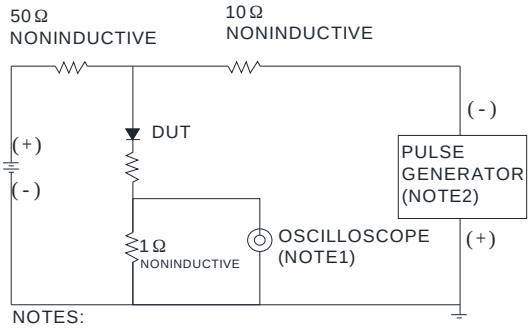
■ (Example)

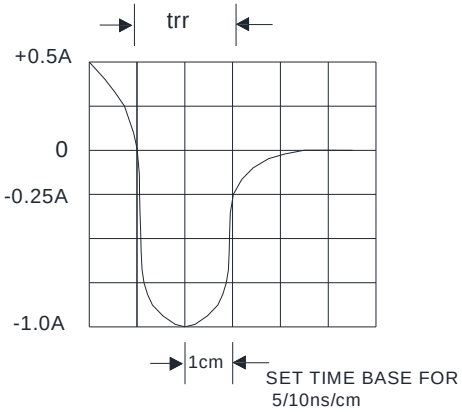
MUR1260L	Approximate 1.8	50	1000	5000	Tube

■ (Typical)

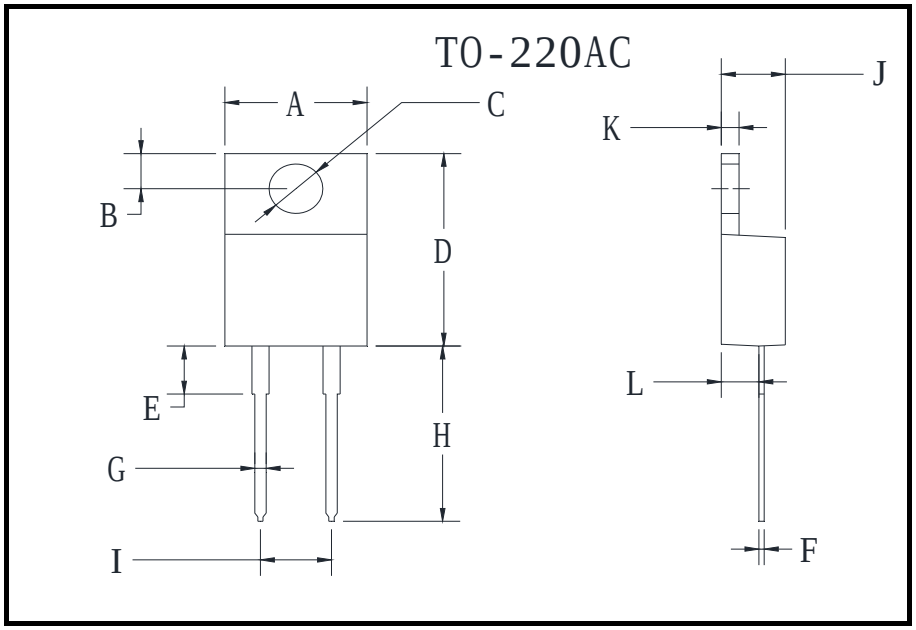

16.0
14.0
12.0
10.0
8.0
6.0
4.0
2.0
0
50
100
150
200
TC measure point


90
1
2
5
10
20
50
100


50Ω
NONINDUCTIVE
10Ω
NONINDUCTIVE
(-)
DUT
(+)
(-)
PULSE
GENERATOR
(NOTE2)
1Ω
NONINDUCTIVE
OSCILLOSCOPE
(NOTE1)
(+)
NOTES:
1.Rise Time=7ns max .Inpot Impedance=1MΩ 22pf
2.Rise Time=10ns max.Sourse Impedance=50Ω


trr
+0.5A
0
-0.25A
-1.0A
1cm
SET TIME BASE FOR
5/10ns/cm

■



Dim	Min	Max
A	9.95	10.35
B	2.55	2.95
C	3.75	4.05
D	14.95	15.25
E	3.75	4.25
F	0.26	0.5
G	0.68	0.94
H	13.3	13.9
I	4.86	5.26
J	4.38	4.78
K	1.14	1.4
L	2.37	2.79

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